762um×762um Silicon PD Chip datasheet

P/N ：WS9J-01A

Application

Si PIN photodiode chips.

Structure

Planar type：PIN diode

Electrodes ：

Top side (Cathode) : Al

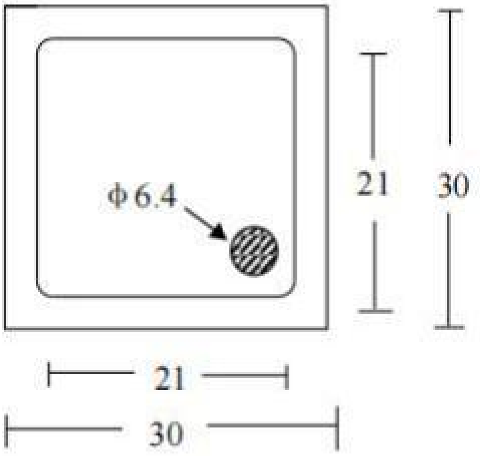
Backside (Anode) ：Au Alloy

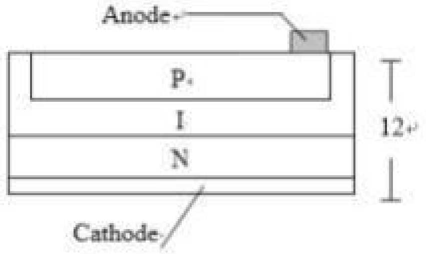
DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	21 ×21 (± 1.0)			mil
Chip width	30 × 30 (± 1.5)			mil
Chip length	30 × 30 (± 1.5)			mil
Chip height	12 (±1.0)			mil
Pad N(Cathode)	6.4 × 6.4			mil
Pad P(Anode)	6.4 × 6.4			mil

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.5		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=3V, F=1 MHz		9		pF





Unit:mil

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